

Manuel Cardona

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/11528383/manuel-cardona-publications-by-year.pdf>

Version: 2024-04-27

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

196
papers

18,549
citations

63
h-index

134
g-index

200
ext. papers

19,623
ext. citations

3.3
avg, IF

6.35
L-index

#	Paper	IF	Citations
196	On the value of author indices. <i>Physics Today</i> , 2011 , 64, 9-10	0.9	1
195	Full-zone analysis of relativistic spin splitting at band anticrossings: The case of zinc-blende semiconductors. <i>Physical Review B</i> , 2010 , 81,	3.3	16
194	Isotope effects on the lattice parameter of cubic SiC. <i>Physical Review B</i> , 2009 , 79,	3.3	8
193	The citation impact outside references [Formal versus informal citations. <i>Scientometrics</i> , 2009 , 80, 1-21	3	12
192	Dielectric constant and long-wavelength refractive index vs. pressure and temperature in semiconductors. <i>High Pressure Research</i> , 2009 , 29, 469-475	1.6	
191	Path-integral molecular dynamics simulation of 3C-BiC. <i>Physical Review B</i> , 2008 , 77,	3.3	20
190	Electronic Band Structures. <i>Graduate Texts in Physics</i> , 2005 , 17-105	0.3	
189	Optical Properties II. <i>Graduate Texts in Physics</i> , 2005 , 345-426	0.3	2
188	Effect of isotope substitution and doping on the Raman spectrum of galena (PbS). <i>Solid State Communications</i> , 2005 , 134, 565-570	1.6	38
187	Isotope effects on the optical spectra of semiconductors. <i>Reviews of Modern Physics</i> , 2005 , 77, 1173-1224	40.5	319
186	Electron-phonon interaction in tetrahedral semiconductors. <i>Solid State Communications</i> , 2005 , 133, 3-18	1.6	123
185	The disaster of the Nazi-power in science as reflected by some leading journals and scientists in physics.. <i>Scientometrics</i> , 2005 , 64, 313-324	3	5
184	Photoelectron Spectroscopy. <i>Graduate Texts in Physics</i> , 2005 , 427-468	0.3	
183	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors. <i>Graduate Texts in Physics</i> , 2005 , 469-551	0.3	
182	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. <i>Graduate Texts in Physics</i> , 2005 , 107-158	0.3	
181	Optical Properties I. <i>Graduate Texts in Physics</i> , 2005 , 243-343	0.3	3
180	Temperature dependence of the energy gap of semiconductors in the low-temperature limit. <i>Physical Review Letters</i> , 2004 , 92, 196403	7.4	68

179	Phonons, Electrons, and Electron-Phonon Interaction: Semiconductors and High-Tc Superconductors 2002 , 257-293		2
178	First- and second-order Raman spectra of galena (PbS). <i>Journal of Applied Physics</i> , 2002 , 92, 4375-4380	2.5	126
177	Dependence of the excitation energies of boron in diamond on isotopic mass. <i>Solid State Communications</i> , 2001 , 121, 7-8	1.6	13
176	Correlation between the Josephson coupling energy and the condensation energy in bilayer cuprate superconductors. <i>Physical Review B</i> , 2001 , 64,	3.3	25
175	Phonons in isotopically modified semiconductors and high Tc superconductors. <i>Physica B: Condensed Matter</i> , 1999 , 263-264, 376-380	2.8	8
174	First principles calculation of the real part of phonon self energy in compound semiconductors. <i>Physica B: Condensed Matter</i> , 1999 , 263-264, 687-690	2.8	19
173	Raman scattering in high Tc superconductors: phonons, electrons, and electron-phonon interaction. <i>Physica C: Superconductivity and Its Applications</i> , 1999 , 317-318, 30-54	1.3	46
172	Phonon anomalies in the far-infrared c-axis conductivity of underdoped YBa ₂ Cu ₃ O _y as Evidence for the intra-bilayer Josephson effect. <i>Journal of Low Temperature Physics</i> , 1999 , 117, 1049-1053	1.3	4
171	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions 1999 , 99-147		3
170	Optical Properties I 1999 , 233-331		4
169	Photoelectron Spectroscopy 1999 , 415-455		
168	Optical Properties II 1999 , 333-413		2
167	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors 1999 , 457-535		
166	Electronic Band Structures 1999 , 13-98		
165	Ellipsometric investigations of piezo-optical effects. <i>Thin Solid Films</i> , 1998 , 313-314, 10-17	2.2	10
164	Phonons, Strains, and Pressure in Semiconductors. <i>Semiconductors and Semimetals</i> , 1998 , 55, 117-233	0.6	35
163	Isotopic mass and lattice constant: X-ray standing wave measurements. <i>Science</i> , 1998 , 282, 930-2	33.3	59
162	Infrared absorption in amorphous silicon from ab initio molecular dynamics. <i>Applied Physics Letters</i> , 1997 , 71, 2692-2694	3.4	35

161	Effects of isotopic composition on the lattice dynamics of CuCl. <i>Physical Review B</i> , 1997 , 56, 210-220	3.3	59
160	Isotopic effects on the lattice constant in compound semiconductors by perturbation theory: An ab initio calculation. <i>Physical Review B</i> , 1996 , 54, 11305-11310	3.3	74
159	Electron-phonon interaction at the direct gap of the copper halides. <i>Solid State Communications</i> , 1996 , 98, 27-30	1.6	30
158	Fundamentals of Semiconductors 1996 ,		733
157	Optical Properties I 1996 , 233-331		5
156	Optical Properties II 1996 , 333-413		1
155	Electronic Band Structures 1996 , 13-98		
154	Photoelectron Spectroscopy 1996 , 415-455		
153	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions 1996 , 99-147		
152	Raman Scattering in Semiconductors with Reduced Translational Invariance. <i>Kluwer International Series in Engineering and Computer Science</i> , 1996 , 141-163		
151	Raman scattering by electronic excitations in semiconductors and in highT c superconductors. <i>Journal of Low Temperature Physics</i> , 1995 , 99, 205-221	1.3	44
150	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. <i>Physical Review B</i> , 1993 , 48, 7915-7929	3.3	73
149	Self-consistent calculation of intervalley deformation potentials in GaAs and Ge. <i>Journal of Applied Physics</i> , 1993 , 74, 2117-2119	2.5	13
148	Effect of heavy doping on the optical properties and band structure of GaAs. <i>Physical Review B</i> , 1993 , 47, 7071-7079	3.3	27
147	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. <i>Thin Solid Films</i> , 1993 , 233, 185-188	2.2	14
146	Linear optical response of semiconductors. <i>Journal of Electronic Materials</i> , 1993 , 22, 27-37	1.9	3
145	Problems in Optical Properties of Semiconductors and their Solutions 1993 , 435-473		
144	Isotope and temperature shifts of direct and indirect band gaps in diamond-type semiconductors. <i>Physical Review B</i> , 1992 , 45, 3376-3385	3.3	100

143	Alloy versus phonon contributions to intervalley scattering in Al _{1-x} Ga _x As 1992 , 1677, 75		3
142	The temperature dependence of the band gaps in InP, InAs, InSb, and GaSb. <i>Solid State Communications</i> , 1991 , 77, 485-488	1.6	48
141	Raman scattering in high-T _c superconductors. <i>Physica C: Superconductivity and Its Applications</i> , 1991 , 185-189, 65-71	1.3	24
140	Microscopic theory of intervalley scattering in InP. <i>Physical Review B</i> , 1991 , 44, 13446-13451	3.3	15
139	Temperature dependence of the dielectric function and the interband critical-point parameters of GaSb. <i>Physical Review B</i> , 1991 , 43, 4349-4360	3.3	70
138	Intervalley scattering times from the rigid-pseudion method 1990 , 1282, 78		7
137	Effective intervalley deformation potentials in the description of time-resolved and hot-electron luminescence. <i>Solid State Communications</i> , 1990 , 76, 877-879	1.6	20
136	Conduction-band minima of InP: Ordering and absolute energies. <i>Applied Physics Letters</i> , 1990 , 57, 2339-2341	3.4	11
135	Ultrafast initial relaxation of hot electrons and holes in tetrahedral semiconductors via deformation potential interaction: Theory and experiment. <i>Applied Physics Letters</i> , 1990 , 57, 2838-2840	3.4	16
134	Microscopic theory of intervalley scattering in GaAs: k dependence of deformation potentials and scattering rates. <i>Journal of Applied Physics</i> , 1990 , 68, 1682-1693	2.5	114
133	Are transverse phonons important for Γ -X intervalley scattering?. <i>Solid-State Electronics</i> , 1989 , 32, 1585-1589		21
132	Intervalley deformation potentials and scattering rates in zinc blende semiconductors. <i>Applied Physics Letters</i> , 1989 , 54, 614-616	3.4	79
131	The dielectric function of AlSb from 1.4 to 5.8 eV determined by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1989 , 66, 383-387	2.5	65
130	Raman spectroscopy of vibrations in superlattices 1989 , 49-152		113
129	Temperature Dependence of the Band Structure of Semiconductors: Electron-Phonon Interaction. <i>Physics and Chemistry of Materials With Low-dimensional Structures</i> , 1989 , 51-64		10
128	Resonant Raman Scattering in Semiconductors. <i>Physica Scripta</i> , 1989 , T25, 201-205	2.6	5
127	X1 and X3 states of electrons and phonons in zincblende type semiconductors. <i>Solid State Communications</i> , 1988 , 67, 927-930	1.6	33
126	Comment on "Spectroscopy of excited states in In _{0.53} Ga _{0.47} As-InP single quantum wells grown by chemical-beam epitaxy". <i>Physical Review B</i> , 1988 , 37, 1011-1012	3.3	29

125	Spin relaxation of holes in the split-hole band of InP and GaSb. <i>Physical Review B</i> , 1987 , 35, 3843-3853	3.3	14
124	Resonant Raman scattering by LO phonons near the E0+ Delta 0 gap of GaSb. <i>Physical Review B</i> , 1987 , 35, 9619-9624	3.3	20
123	Resonant Raman scattering by plasmons and LO phonons near the E1 and E1+ Delta 1 gaps of GaSb. <i>Physical Review B</i> , 1987 , 36, 7469-7485	3.3	32
122	Acoustic deformation potentials and heterostructure band offsets in semiconductors. <i>Physical Review B</i> , 1987 , 35, 6182-6194	3.3	489
121	Vibrations in amorphous silicon and its alloys. <i>Journal of Molecular Structure</i> , 1986 , 141, 93-107	3.4	15
120	Comment on "g-factor anisotropy of conduction electrons in InSb". <i>Physical Review B</i> , 1986 , 34, 7402-7403	3.3	15
119	Resonant Raman scattering and interference effects of LO phonons at the E0+ Delta 0 gap of InP. <i>Physical Review B</i> , 1986 , 33, 5473-5481	3.3	63
118	Dependence of the direct energy gap of GaP on hydrostatic pressure. <i>Solid State Communications</i> , 1985 , 55, 327-331	1.6	46
117	Light emission at the E1 and E1+ Γ_1 gaps in heavily doped p-type Ge and GaAs. <i>Solid State Communications</i> , 1985 , 56, 549-552	1.6	1
116	Electron and phonon self-energies in heavily doped germanium and silicon. <i>Solid-State Electronics</i> , 1985 , 28, 31-38	1.7	1
115	Resonant Raman scattering by spin-density fluctuations in n-type germanium. <i>Physical Review Letters</i> , 1985 , 55, 1132-1135	7.4	11
114	Resonance Raman scattering by LO phonons in CdxHg1-xTe at the E0+ Delta 0 gap. <i>Physical Review B</i> , 1985 , 31, 3705-3711	3.3	69
113	Electronic Raman scattering in heavily doped p-type germanium. <i>Physical Review B</i> , 1985 , 32, 8071-8077	3.3	18
112	Interference effects: A key to understanding forbidden Raman scattering by LO phonons in GaAs. <i>Physical Review B</i> , 1985 , 31, 3696-3704	3.3	152
111	Light scattering by plasmons in germanium. <i>Physical Review B</i> , 1984 , 29, 3737-3739	3.3	17
110	Electron-phonon interaction and phonon softening in ferro-electrics and semiconductors. <i>Ferroelectrics</i> , 1984 , 53, 49-58	0.6	4
109	Resonant Raman scattering by plasmons in n-type Ge. <i>Solid State Communications</i> , 1984 , 49, 1103-1105	1.6	2
108	Temperature dependence of the first-order Raman scattering by phonons in Si, Ge, and Sn: Anharmonic effects. <i>Physical Review B</i> , 1984 , 29, 2051-2059	3.3	619

107	Light scattering by free carrier excitations in semiconductors. <i>Topics in Applied Physics</i> , 1984 , 5-150	0.5	123
106	Optical constants of pure and heavily doped silicon and germanium: Electronic interband transitions. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983 , 117-118, 356-358		2
105	Interference between Allowed and Forbidden Raman Scattering by Longitudinal-Optical Phonons in GaAs. <i>Physical Review Letters</i> , 1983 , 51, 1297-1299	7.4	51
104	Vibrational spectra of a-Si: H, a-Si: F, and a-Ge: F: Bethe-lattice calculations. <i>Physical Review B</i> , 1983 , 28, 880-888	3.3	26
103	Pressure dependence of Raman phonons of Ge and 3C-SiC. <i>Physical Review B</i> , 1982 , 25, 1151-1160	3.3	160
102	Temperature dependence of the optical phonons and transverse effective charge in 3C-SiC. <i>Physical Review B</i> , 1982 , 25, 3889-3896	3.3	79
101	Self-energy effects of the optical phonons of heavily doped p-GaAs and p-Ge. <i>Physical Review B</i> , 1981 , 23, 6592-6602	3.3	76
100	Raman scattering by two LO-phonons near Γ in GaAs. <i>Solid State Communications</i> , 1981 , 39, 1071-1075	1.6	25
99	A new application of the diamond anvil cell: Measurements under uniaxial stress. <i>Solid State Communications</i> , 1981 , 38, 1109-1112	1.6	10
98	Resonant spin-flip Raman scattering on donor and acceptor states in ZnTe. <i>Physical Review B</i> , 1981 , 23, 4129-4139	3.3	41
97	Intra- and inter-valence-band electronic Raman scattering in heavily doped p-GaAs. <i>Physical Review B</i> , 1980 , 22, 1905-1911	3.3	17
96	Photoluminescence in heavily doped GaAs. II. Hydrostatic pressure dependence. <i>Physical Review B</i> , 1980 , 22, 894-903	3.3	76
95	Electronic properties of clean and oxygen covered (100) cleaved surfaces of PbS. <i>Surface Science</i> , 1980 , 92, 385-392	1.8	22
94	Photoluminescence in heavily doped GaAs. I. Temperature and hole-concentration dependence. <i>Physical Review B</i> , 1980 , 22, 886-893	3.3	156
93	Luminescence above the gap in heavily Zn-doped GaAs. <i>Solid State Communications</i> , 1979 , 32, 1027-1030	1.6	8
92	Temperature effects on valence bands in semiconducting lead chalcogenides. <i>Solid State Communications</i> , 1979 , 32, 353-356	1.6	11
91	Raman scattering in pure and hydrogenated amorphous germanium and silicon. <i>Journal of Non-Crystalline Solids</i> , 1979 , 32, 405-419	3.9	174
90	Infrared absorption in hydrogenated amorphous and crystallized germanium. <i>Journal of Non-Crystalline Solids</i> , 1979 , 32, 421-430	3.9	72

89	Piezoresistance and the conduction-band minima of GaAs. <i>Physical Review B</i> , 1978 , 17, 741-751	3.3	39
88	Strain dependence of effective masses in tetrahedral semiconductors. <i>Physical Review B</i> , 1978 , 17, 726-740	3.3	45
87	Angle-resolved uv photoemission and electronic band structures of the lead chalcogenides. <i>Physical Review B</i> , 1978 , 18, 3847-3871	3.3	119
86	Effect of hydrostatic pressure on the direct absorption edge of germanium. <i>Physical Review B</i> , 1977 , 15, 875-879	3.3	59
85	Valence Band Structure of PbS from Angle-Resolved Photoemission. <i>Physical Review Letters</i> , 1977 , 38, 1033-1036	7.4	54
84	Intraband Raman scattering by free carriers in heavily doped nBi. <i>Physical Review B</i> , 1977 , 16, 3579-3595	3.3	57
83	Transverse reduced mass of the E1 and E1+ π transitions in silicon. <i>Physical Review B</i> , 1977 , 15, 5999-6000	3.3	31
82	Resonant Raman scattering in ZnO. <i>Physical Review B</i> , 1977 , 16, 3753-3761	3.3	707
81	Infrared and Raman spectra of the silicon-hydrogen bonds in amorphous silicon prepared by glow discharge and sputtering. <i>Physical Review B</i> , 1977 , 16, 3556-3571	3.3	1477
80	Resonant Raman scattering in the II-IV semiconductors Mg ₂ Si, Mg ₂ Ge, and Mg ₂ Sn. <i>Physical Review B</i> , 1976 , 14, 3520-3531	3.3	30
79	Valence bands of the Mg ₂ X(X=Si, Ge, Sn) semiconducting compounds. <i>Physical Review B</i> , 1976 , 14, 2559-2568	3.3	35
78	Effect of free carriers on the elastic constants of p-type silicon and germanium. <i>Physical Review B</i> , 1976 , 13, 5429-5441	3.3	21
77	Dependence of the indirect energy gap of silicon on hydrostatic pressure. <i>Solid State Communications</i> , 1975 , 17, 1021-1024	1.6	83
76	Dependence of the direct energy gap of GaAs on hydrostatic pressure. <i>Physical Review B</i> , 1975 , 12, 5729-5738	3.3	287
75	Bond Charge, Bond Polarizability, and Phonon Spectra in Semiconductors. <i>Physical Review Letters</i> , 1975 , 34, 580-583	7.4	131
74	Densities of valence states of amorphous and crystalline III-V and II-VI semiconductors. <i>Physical Review B</i> , 1974 , 9, 2627-2648	3.3	210
73	Interaction between electronic and vibronic Raman scattering in heavily doped silicon. <i>Solid State Communications</i> , 1973 , 13, 325-328	1.6	76
72	Elastic constants and Raman frequencies of heavily doped Si under uniaxial stress. <i>Solid State Communications</i> , 1973 , 12, 553-556	1.6	6

71	Light scattering as a form of modulation spectroscopy. <i>Surface Science</i> , 1973 , 37, 100-119	1.8	46
70	Effects of Free Carriers on Zone-Center Vibrational Modes in Heavily Doped p-type Si. I. Acoustical Modes. <i>Physical Review B</i> , 1973 , 8, 4723-4733	3.3	21
69	Resonant First- and Second-Order Raman Scattering in GaP. <i>Physical Review B</i> , 1973 , 8, 2795-2809	3.3	111
68	Second-Order Raman Spectrum of Germanium. <i>Physical Review B</i> , 1973 , 7, 2545-2551	3.3	96
67	Effect of Carrier Concentration on the Raman Frequencies of Si and Ge. <i>Physical Review B</i> , 1972 , 5, 1440-1454	3.5	194
66	Stress-Induced Shifts of First-Order Raman Frequencies of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1972 , 5, 580-593	3.3	779
65	Two-phonon Raman spectra of Si and GaP. <i>Solid State Communications</i> , 1972 , 10, 961-965	1.6	36
64	Resonant Raman scattering in germanium. <i>Solid State Communications</i> , 1972 , 10, 591-595	1.6	86
63	X-ray and far ultraviolet photoemission of AlSb. <i>Solid State Communications</i> , 1972 , 11, 1619-1623	1.6	29
62	Photoemission of GaAs and InSb core levels. <i>Solid State Communications</i> , 1972 , 11, 1655-1658	1.6	16
61	Resonant Raman scattering in germanium and zincblende-type semiconductors temperature dependence. <i>Solid State Communications</i> , 1971 , 9, 1235-1238	1.6	14
60	Spatial dispersion in the dielectric constant of GaAs. <i>Solid State Communications</i> , 1971 , 9, 1421-1424	1.6	58
59	Effects of Uniaxial Stress on the Indirect Exciton Spectrum of Silicon. <i>Physical Review B</i> , 1971 , 3, 2623-2636	3.6	218
58	Modulation Spectroscopy of Semiconductors 1970 , 125-173		22
57	Optical Properties of Some Compound Semiconductors in the 36-150-eV Region. <i>Physical Review B</i> , 1970 , 1, 2605-2612	3.3	53
56	Deformation Potentials of the Indirect and Direct Absorption Edges of AlSb. <i>Physical Review B</i> , 1970 , 1, 1436-1442	3.3	40
55	Energy-Band Structure and Optical Spectrum of Grey Tin. <i>Physical Review B</i> , 1970 , 2, 352-363	3.3	64
54	Anomalous Behavior of Hc_3Hc_2 near T_c for Sn-In and In-Bi Alloy Systems. <i>Physical Review B</i> , 1970 , 2, 2513-2519	3.3	196

53	Modulated Piezoreflectance in Semiconductors. <i>Physical Review B</i> , 1970 , 1, 672-682	3.3	160
52	Modulation spectroscopy of semiconductors 1970 , 125-173		8
51	Transverse electroreflectance in semi-insulating silicon and gallium arsenide. <i>Journal of Physics and Chemistry of Solids</i> , 1970 , 31, 227-246	3.9	49
50	Temperature Coefficient of the Refractive Index of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1970 , 2, 3193-3197	3.3	101
49	Piezobirefringence and Deformation Potentials of the Alkali Halides. <i>Physical Review</i> , 1969 , 177, 1351-1357		47
48	Variation of the Ratio $H_{c3}H_{c2}$ in the Immediate Vicinity of T_c . <i>Physical Review</i> , 1969 , 187, 766-767		12
47	Stress-Induced Exchange Splitting of Hyperbolic Excitons in GaAs.. <i>Physical Review Letters</i> , 1969 , 22, 933-936	4.6	48
46	Photoreflectance and electroreflectance in silicon. <i>Solid State Communications</i> , 1969 , 7, 879-882	1.6	32
45	Intrinsic piezobirefringence of AlSb. <i>Solid State Communications</i> , 1969 , 7, 1113-1117	1.6	14
44	Derivative spectrum of indirect excitons in AlSb. <i>Solid State Communications</i> , 1969 , 7, 441-444	1.6	22
43	Intrinsic Piezobirefringence of Ge, Si, and GaAs. <i>Physical Review</i> , 1969 , 184, 821-829		144
42	Optical Constants of Insulators: Dispersion Relations 1969 , 137-151		23
41	New Evidence for the Existence of Exciton Effects at Hyperbolic Critical Points. <i>Physical Review</i> , 1968 , 174, 828-830		81
40	Piezo-Electroreflectance in Ge, GaAs, and Si. <i>Physical Review</i> , 1968 , 172, 816-837		798
39	Thermoreflectance in Semiconductors. <i>Physical Review</i> , 1968 , 176, 950-960		227
38	Valence band symmetry and deformation potentials of ZnO. <i>Solid State Communications</i> , 1968 , 6, 239-242		53
37	Thermoreflectance in the alkali metals. <i>Solid State Communications</i> , 1968 , 6, 313-316	1.6	13
36	Electroreflectance Measurements on Mg ₂ Si, Mg ₂ Ge, and Mg ₂ Sn. <i>Physical Review</i> , 1968 , 176, 905-908		53

35	Chapter 5 Optical Absorption above the Fundamental Edge. <i>Semiconductors and Semimetals</i> , 1967 , 3, 125-151	0.6	6
34	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review</i> , 1967 , 154, 696-720		715
33	Band structure of gray tin under uniaxial stress. <i>Solid State Communications</i> , 1967 , 5, 233-235	1.6	20
32	Optical constants of germanium and gray tin the . method. <i>Solid State Communications</i> , 1967 , 5, 513-516	1.6	25
31	Energy band structure of germanium and gallium arsenide: The . method. <i>Journal of Physics and Chemistry of Solids</i> , 1966 , 27, 423-425	3.9	32
30	Electroreflectance and band structure of gray tin. <i>Solid State Communications</i> , 1966 , 4, 319-321	1.6	38
29	Electronic surface states in germanium and silicon. <i>Solid State Communications</i> , 1966 , 4, 271-274	1.6	27
28	Energy-Band Structure of Germanium and Silicon: The $k\Gamma$ Method. <i>Physical Review</i> , 1966 , 142, 530-543		550
27	Electroreflectance in AlSb: Observation of the Direct Band Edge. <i>Physical Review Letters</i> , 1966 , 16, 644-646	7.4	35
26	Electroreflectance and Spin-Orbit Splitting in III-V Semiconductors. <i>Physical Review Letters</i> , 1966 , 16, 48-50	7.4	43
25	Piezoelectroreflectance in GaAs. <i>Physical Review Letters</i> , 1966 , 16, 942-944	7.4	46
24	Electroreflectance in the GaAs-GaP Alloys. <i>Physical Review</i> , 1966 , 146, 601-610		153
23	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review Letters</i> , 1965 , 15, 883-885	7.4	103
22	Infrared Dielectric Constant and Ultraviolet Optical Properties of Solids with Diamond, Zinc Blende, Wurtzite, and Rocksalt Structure. <i>Journal of Applied Physics</i> , 1965 , 36, 2181-2186	2.5	83
21	Ultraviolet Reflection Spectrum of Cubic CdS. <i>Physical Review</i> , 1965 , 140, A633-A637		123
20	Optical Properties and Band Structure of Wurtzite-Type Crystals and Rutile. <i>Physical Review</i> , 1965 , 137, A1467-A1476		474
19	Optical Properties and Band Structure of SrTiO ₃ and BaTiO ₃ . <i>Physical Review</i> , 1965 , 140, A651-A655		661
18	Evidence for Normal Regions at Low Temperatures in the Superconducting Mixed State. <i>Physical Review Letters</i> , 1964 , 12, 657-659	7.4	62

17	Microwave Surface Impedance of Superconductors of the Second Kind: In-Bi Alloys. <i>Physical Review Letters</i> , 1964 , 12, 101-103	7.4	24
16	Optical Properties and Band Structure of Group IV-VI and Group V Materials. <i>Physical Review</i> , 1964 , 133, A1685-A1697		359
15	Polarization effects in the ultraviolet reflection of crystals with wurtzite structure. <i>Solid State Communications</i> , 1963 , 1, 109-115	1.6	38
14	Band parameters of semiconductors with zincblende, wurtzite, and germanium structure. <i>Journal of Physics and Chemistry of Solids</i> , 1963 , 24, 1543-1555	3.9	401
13	Absorption Spectrum of Germanium and Zinc-Blende-Type Materials at Energies Higher than the Fundamental Absorption Edge. <i>Journal of Applied Physics</i> , 1963 , 34, 813-818	2.5	148
12	Fundamental Reflectivity and Band Structure of ZnTe, CdTe, and HgTe. <i>Physical Review</i> , 1963 , 131, 98-103		255
11	Optical Properties of the Silver and Cuprous Halides. <i>Physical Review</i> , 1963 , 129, 69-78		538
10	Resonances of a Small Plasma Sphere in a Magnetic Field. <i>Physical Review</i> , 1963 , 129, 991-997		29
9	Reflectivity of Semiconductors with Wurtzite Structure. <i>Physical Review</i> , 1963 , 129, 1068-1069		50
8	Excitons at the L Absorption Edge in Zinc Blende-Type Semiconductors. <i>Physical Review Letters</i> , 1962 , 8, 90-91	7.4	62
7	Reflectivity of Gray Tin Single Crystals in the Fundamental Absorption Region. <i>Physical Review</i> , 1962 , 125, 1291-1296		94
6	Faraday rotation in semiconductors 1962 , 72-88		
5	Electron Effective Masses of InAs and GaAs as a Function of Temperature and Doping. <i>Physical Review</i> , 1961 , 121, 752-758		175
4	Optical Studies of the Band Structure of InP. <i>Journal of Applied Physics</i> , 1961 , 32, 958-958	2.5	50
3	Fundamental Reflectivity Spectrum of Semiconductors with Zinc-Blende Structure. <i>Journal of Applied Physics</i> , 1961 , 32, 2151-2155	2.5	154
2	Optical investigation of the band structure of GaSb. <i>European Physical Journal A</i> , 1961 , 161, 99-102	2.5	27
1	Effect of Temperature and Doping on the Reflectivity of Germanium in the Fundamental Absorption Region. <i>Physical Review</i> , 1961 , 122, 1382-1388		85